

## Isc N-Channel MOSFET Transistor

## STB11NM60FD

### • FEATURES

- With To-263(D2PAK) package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • APPLICATIONS

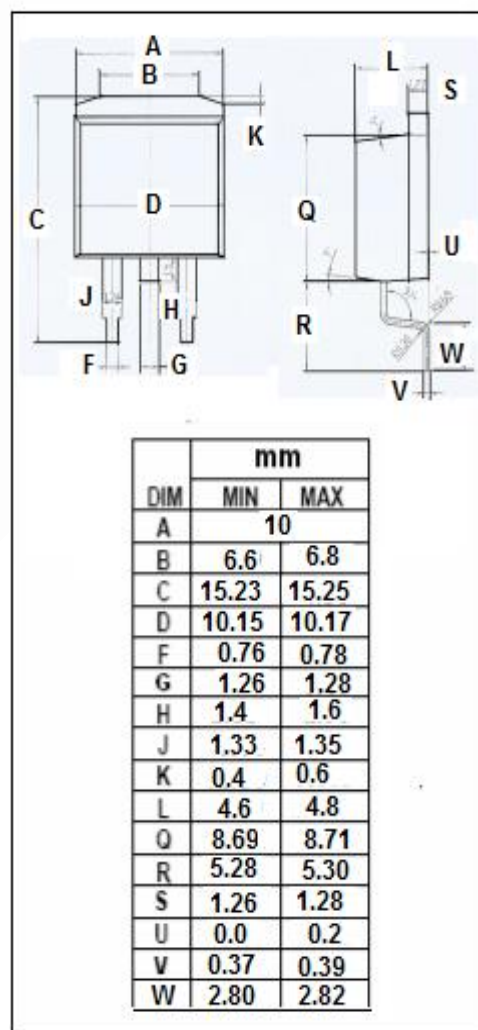
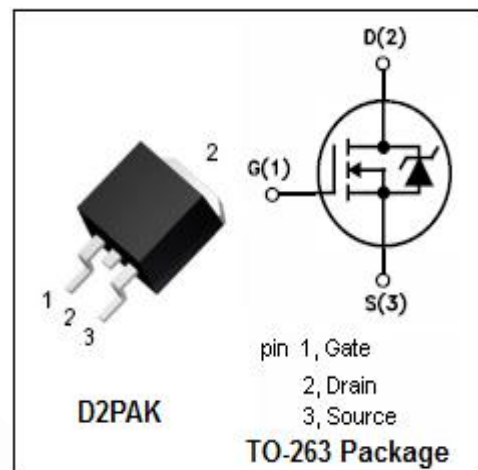
- Switching applications

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	600	V
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=125^{\circ}\text{C}$	11 7	A
$I_{DM}$	Drain Current-Single Pulsed	44	A
$P_D$	Total Dissipation @ $T_c=25^{\circ}\text{C}$	160	W
$T_{ch}$	Max. Operating Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-65~150	$^{\circ}\text{C}$

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.78	$^{\circ}\text{C}/\text{W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62.5	$^{\circ}\text{C}/\text{W}$



**Isc N-Channel MOSFET Transistor****STB11NM60FD****ELECTRICAL CHARACTERISTICS**T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	600			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = ±30V; I <sub>D</sub> =0.25mA	3		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =5.5A		400	450	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0V; T <sub>J</sub> =25°C T <sub>J</sub> =125°C			1 100	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =11A, V <sub>GS</sub> = 0 V			1.5	V